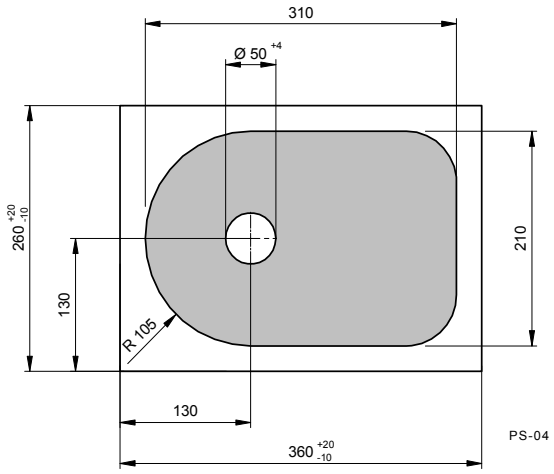
LED - Chip

ELC-630-29-20

Preliminary 10.04.2007 rev. 02/06

Radiation	Type	Technology	Electrodes
Red	Point Source	AlInGaP/GaAs	N (cathode) up



typ. dimensions (µm)

typ. thickness
170 (±20) µm

cathode
gold alloy, 1.5 µm

anode
gold alloy, 0.5 µm

Maximum Ratings

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I_F			15	mA

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F = 10 mA	V_F		2.3	2.6	V
Reverse voltage	I_R = 10 µA	V_R	5			V
Radiant power*	I_F = 10 mA	Φ_e	70	130		µW
Luminous intensity*	I_F = 10 mA	I_V	3.0	5.5		mcd
Peak wavelength	I_F = 10 mA	λ_P	625	630	635	nm
Spectral bandwidth at 50%	I_F = 10 mA	$\Delta\lambda_{0.5}$		17		nm
Switching time	I_F = 10 mA	t_r, t_f		40/30		ns

*Measured on bare chip on TO-18 header with *EPIGAP* equipment

Labeling

Type	Lot N°	I_V(typ) [mcd]	V_F(typ) [V]	Quantity
ELC-630-29-20				

Packing: Chips on adhesive film with wire-bond side on top

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